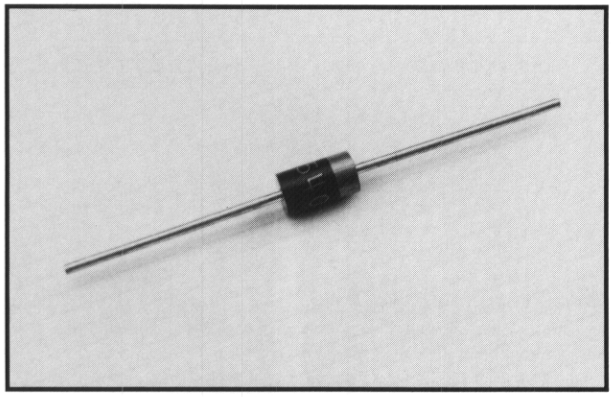
1N5400 Thru 1N5408

3 AMP PLASTIC SILICON RECTIFIER

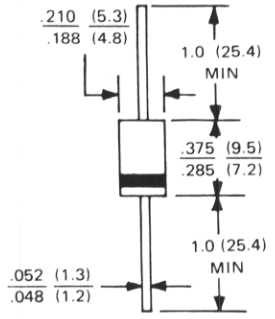


FEATURES

- Rating to 1000V PRV
- Low cost
- Diffused junction
- Low leakage
- Low forward voltage drop
- High current capability
- Easily cleaned with freon, alcohol, chlorothene and similar solvents
- UL recognized 94V-O plastic material

Outline Drawing

DO-201AD



Dimensions in inches and (millimeters)

Mechanical Data

- Case: JEDEC DO-201AD
- Terminals: Axial leads, solderable per MIL-STD-202, Method 208
- Polarity: Color band denotes cathode
- Weight: 0.04 ounce, 1.1 grams
- Mounting Position: Any

Maximum Ratings & Characteristics

- Ratings at 25° C ambient temperature unless otherwise specified
- Single phase, half wave, 60Hz, resistive or inductive load
- For capacitive load, derate current by 20%

		1N5400	1N5401	1N5402	1N5403	1N5404	1N5405	1N5406	1N5407	1N5408	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	500	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	350	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	500	600	800	1000	V
Maximum Average Forward @ T_L = 90°C Rectified Current, .500" (12.7mm) Lead Length	$I_{(AV)}$	3.0									A
Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave Superimposed On Rated Load	I_{FSM}	200									A
Maximum Forward Voltage At 3.0A DC	V_F	1.0									V
Maximum DC Reverse Current @ T_A = 25°C At Rated DC Blocking Voltage @ T_A = 150°C	I_R	10 100									μA
Typical Junction Capacitance (Note 1)	C_J	50						25			pF
Typical Thermal Resistance (Note 2)	R_{thJA}	15									°C/W
Operating Temperature Range	T_J	-65 to +175									°C
Storage Temperature Range	T_{STG}	-65 to +175									°C

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0V DC
2. Thermal resistance Junction to Ambient